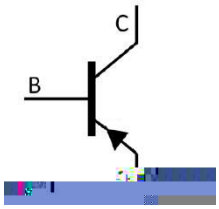
SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

, , 2SC2881G

High f_T, high V_{CEO}



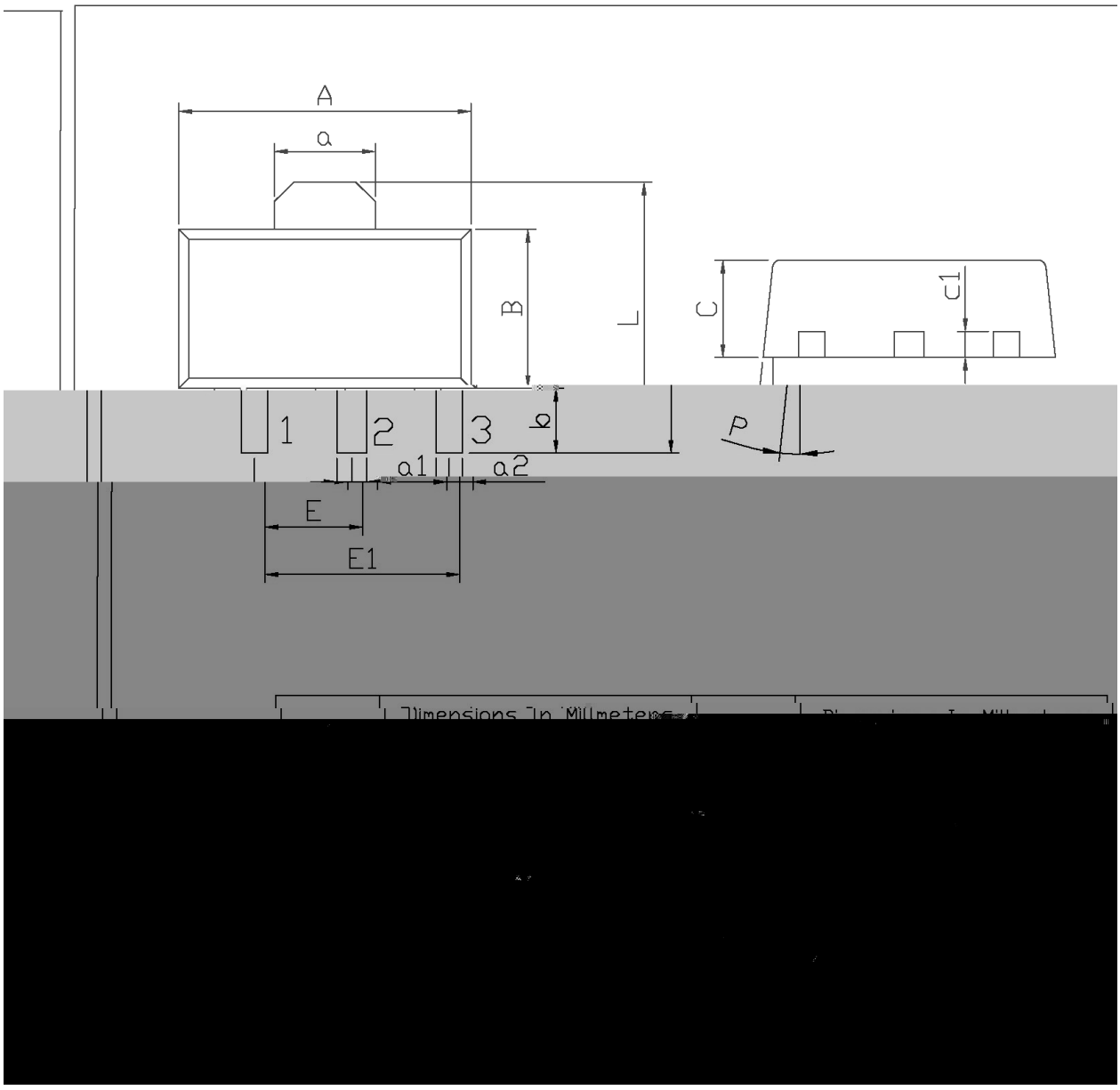
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-800	mA
Collector Base-Continuous	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation*	$*P_C$	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*mounted on ceramic substrate(250mm^2×0.8t)

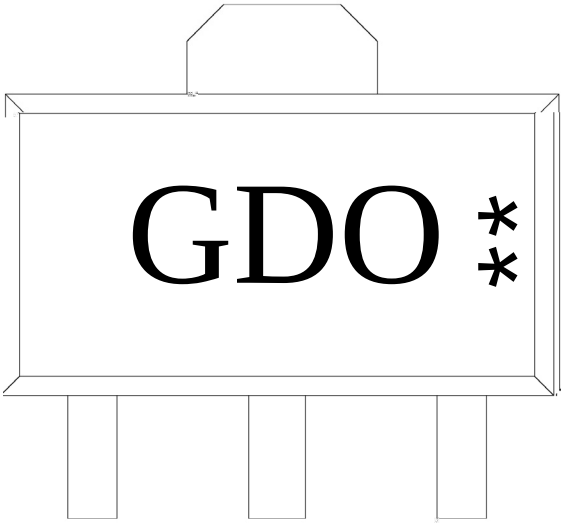
* 250mm^2×0.8t

Parameter	Symbol	Test Conditions

/ Package Dimensions



/ Marking Instructions



G

D

O h_{FE}

**

Note:

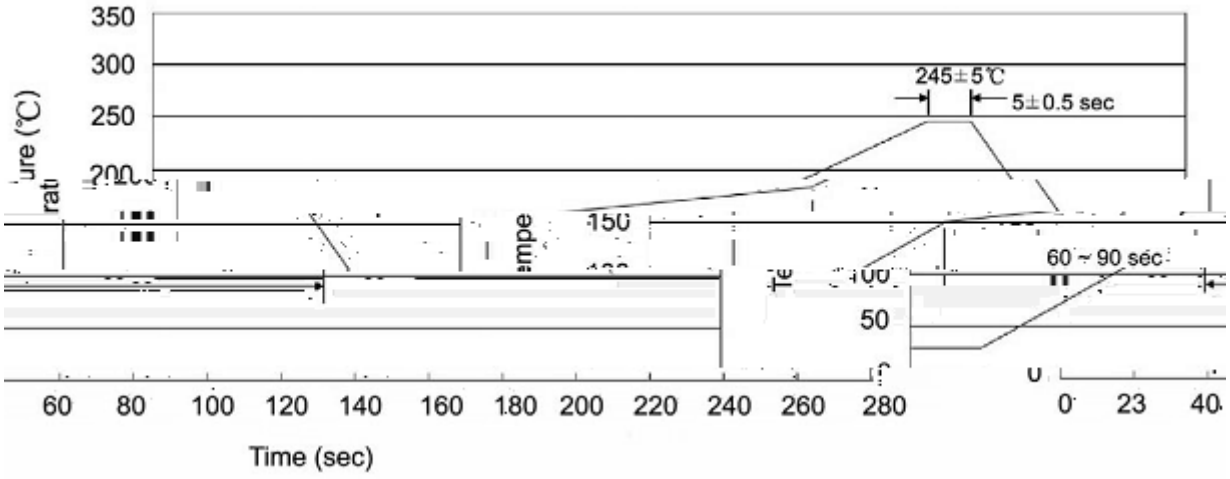
G: Halogen Free Product.

D: Product Type.

O: h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

( ) /



Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

2 245±5 5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3 2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)

/ Notices